

# SILICON POWER TRANSISTORS

## 2SC4332, 2SC4332-Z

### NPN SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SC4332 and 2SC4332-Z are mold power transistors developed for high-speed switching and features a very low collector-to-emitter saturation voltage.

This transistor is ideal for use in switching regulators, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for high-current switching.

#### FEATURES

- Low collector saturation voltage  
 $V_{CE(sat)} = 0.3 \text{ V MAX. (I}_C = 3 \text{ A / I}_B = 0.15 \text{ A)}$
- Fast switching speed:  
 $t_f \leq 0.3 \mu\text{s MAX. (I}_C = 3 \text{ A)}$
- High DC current gain

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

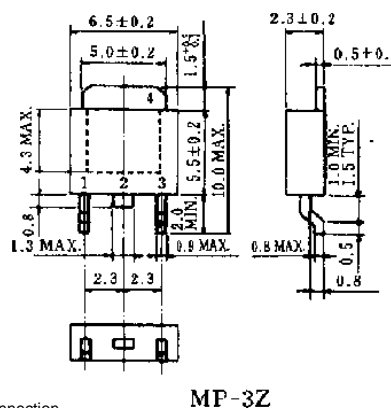
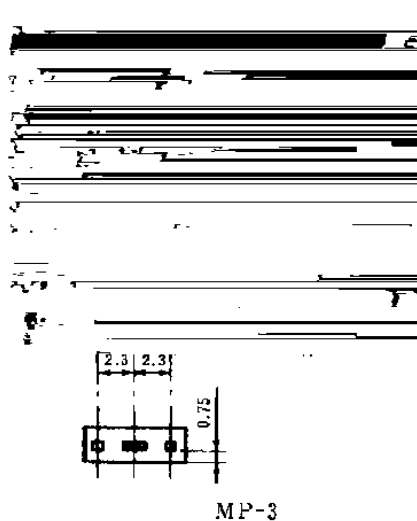
Collector to Base Voltage	$V_{CBO}$	100	V
Collector to Emitter Voltage	$V_{CEO}$	60	V
Base to Emitter Voltage	$V_{EBO}$	7.0	V
Collector Current (DC)	$I_{C(DC)}$	5.0	A
Collector Current (pulse)	$I_{C(pulse)}$ <sup>Note1</sup>	10	A
Base Current (DC)	$I_{B(DC)}$	2.5	A
Total Power Dissipation	$P_T$ ( $T_C = 25^\circ\text{C}$ )	15	W
Total Power Dissipation	$P_T$ ( $T_A = 25^\circ\text{C}$ )	1.0 <sup>Note2</sup> , 2.0 <sup>Note3</sup>	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Notes** 1.  $PW \leq 10 \text{ ms}$ , duty cycle  $\leq 50\%$

2. Printing board mounted

3.  $7.5 \text{ mm}^2 \times 0.7 \text{ mm}$ , ceramic board mounted

#### PACKAGE DRAWING (Unit: mm)



Electrode Connection

1. Base
2. Collector
3. Emitter
4. Fin (collector)

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ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

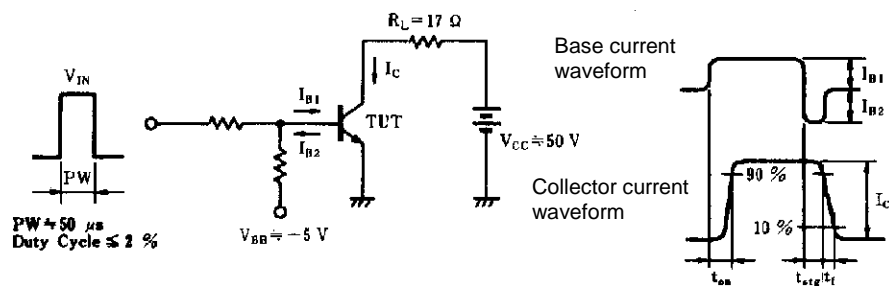
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to Emitter Voltage	V <sub>CEQ(SUS)</sub>	I <sub>C</sub> = 3.0 A, I <sub>B</sub> = 0.3 A, L = 1 mH	60			V
Collector to Emitter Voltage	V <sub>CEX(SUS)</sub>	I <sub>C</sub> = 3.0 A, I <sub>B1</sub> = -I <sub>B2</sub> = 0.3 A, V <sub>BE(OFF)</sub> = -1.5 V, L = 180 μH, clamped	60			V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CE</sub> = 60 V, I <sub>E</sub> = 0			10	μA
Collector Cut-off Current	I <sub>CER</sub>	V <sub>CE</sub> = 60 V, R <sub>BE</sub> = 51 Ω, T <sub>A</sub> = 125°C			1.0	mA
Collector Cut-off Current	I <sub>CEx1</sub>	V <sub>CE</sub> = 60 V, V <sub>BE(OFF)</sub> = -1.5 V			10	μA
Collector Cut-off Current	I <sub>CEx2</sub>	V <sub>CE</sub> = 60 V, V <sub>BE(OFF)</sub> = -1.5 V, T <sub>A</sub> = 125°C			1.0	mA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0			10	μA
DC Current Gain	h <sub>FE1</sub> <sup>Note</sup>	V <sub>CE</sub> = 2.0 V, I <sub>C</sub> = 0.5 A	100			
DC Current Gain	h <sub>FE2</sub> <sup>Note</sup>	V <sub>CE</sub> = 2.0 V, I <sub>C</sub> = 1.0 A	100		400	
DC Current Gain	h <sub>FE3</sub> <sup>Note</sup>	V <sub>CE</sub> = 2.0 V, I <sub>C</sub> = 3.0 A	60			
Collector Saturation Voltage	V <sub>CE(sat)1</sub> <sup>Note</sup>	I <sub>C</sub> = 3.0 A, I <sub>B</sub> = 0.15 A			0.3	V
Collector Saturation Voltage	V <sub>CE(sat)2</sub> <sup>Note</sup>	I <sub>C</sub> = 4.0 A, I <sub>B</sub> = 0.2 A			0.5	V
Base Saturation Voltage	V <sub>BE(sat)1</sub> <sup>Note</sup>	I <sub>C</sub> = 3.0 A, I <sub>B</sub> = 0.15 A			1.2	V
Base Saturation Voltage	V <sub>BE(sat)2</sub> <sup>Note</sup>	I <sub>C</sub> = 4.0 A, I <sub>B</sub> = 0.2 A			1.5	V
Collector Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		130		pF
Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>E</sub> = -0.5 A		150		MHz
Turn-on Time	t <sub>on</sub>	I <sub>C</sub> = 3.0 A, R <sub>L</sub> = 16.7 Ω, I <sub>B1</sub> = -I <sub>B2</sub> = 0.15 A, V <sub>CC</sub> ≈ 50 V Refer to the test circuit.			0.3	μs
Storage Time	t <sub>stg</sub>				1.5	μs
Fall Time	t <sub>f</sub>				0.3	μs

**Note** Pulse test PW ≤ 350 μs, duty cycle ≤ 2%

h<sub>FE</sub> CLASSIFICATION

Marking	M	L	K
h <sub>FE2</sub>	100 to 200	150 to 300	200 to 400

SWITCHING TIME (t<sub>on</sub>, t<sub>stg</sub>, t<sub>f</sub>) TEST CIRCUIT



[MEMO]

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